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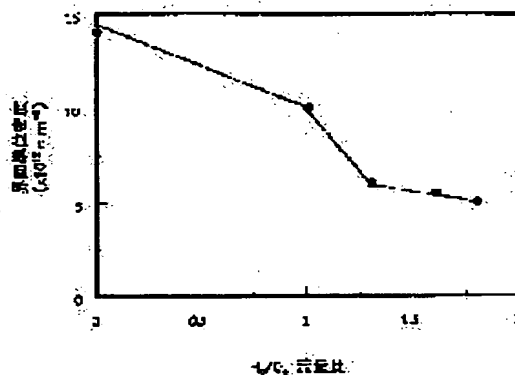
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## (54) METHOD FOR FORMING THERMAL OXIDIZED FILM FOR SILICON CARBIDE SEMICONDUCTOR DEVICE

(57)Abstract:

**PROBLEM TO BE SOLVED:** To reduce surface level density after the formation of a thermal, oxidized film for a silicon carbide semiconductor device.

**SOLUTION:** A thermal oxidized film forming method consists of growing a silicon oxide film by pyrogenic oxidation which causes thermal oxidation by introducing hydrogen oxygen. The flow ratio of hydrogen and oxygen is set 1:1, the flow of hydrogen is made larger than that of oxygen. After oxidation, the film is cooled in an atmosphere containing hydrogen at a rate in the range of 0.3-3°C/min. The temperature for taking the film out after cooling is set to 900°C or less.



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